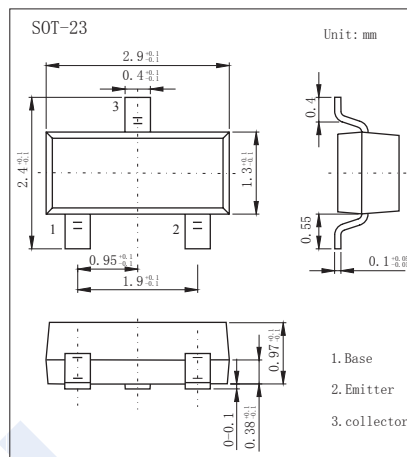


## PNP Transistors

### KST8550S

#### ■ Features

- Collector current:  $I_c = -0.5A$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CE0}$	-25	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current -Continuous	$I_c$	-0.5	A
Collector Power Dissipation	$P_c$	0.3	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CE0}$	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector cut-off current	$I_{CB0}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CE0}$	$V_{CE} = -20V, I_B = 0$			-1	$\mu A$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -3V, I_c = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_c = -50mA$	120		400	
		$V_{CE} = -1V, I_c = -500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_c = -20mA, f = 30MHz$	150			MHz

#### ■ Classification of $h_{FE}(1)$

Type	KST8550S	KST8550S-L	KST8550S-H	KST8550S-J
Range	200-350	120-200	144-202	300-400
Marking	2TY			

# KST8550S

## Typical Characteristics

